May 2024



# **FAN7387** Self-Oscillated, High-Voltage Gate Driver

### **Features**

- Internal Clock Using RCT
- External Sync Function Using RCT
- **Dead Time Control Using Resistor**
- Shut Down (Disable Mode)
- Internal Shunt Regulator
- UVLO Function, High and Low Side

### **Applications**

- Half-Bridge Inverter
- SMPS
- ENTATIVE FO Ballast Solution for High-Intensity Decenarge (HID) Lamp
- Ballast for upro

### Description

The FAN7387 is a mpi cer ul IC for common half-SMI ar. oallas for Iuorescent and bridge invert⊾ HID lamp. The AN7 7 has a oscillating circuit using a capac tor. rnal sisi. an

e que, variation is very stand across a wide te per vre range. The FAN7??? has an emernal pin for ad-ume control and shortown. Using this resistor, the designer can choose the optimum dead time to educe onwer loss on switching devices, such as transistors and MCSFETs.

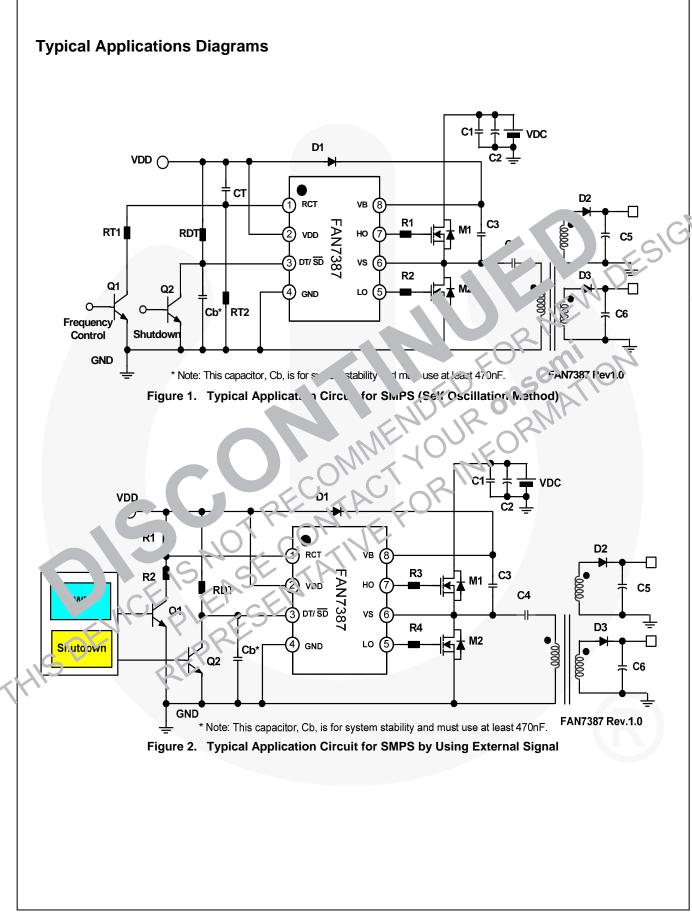
> S DIP 8-SOP

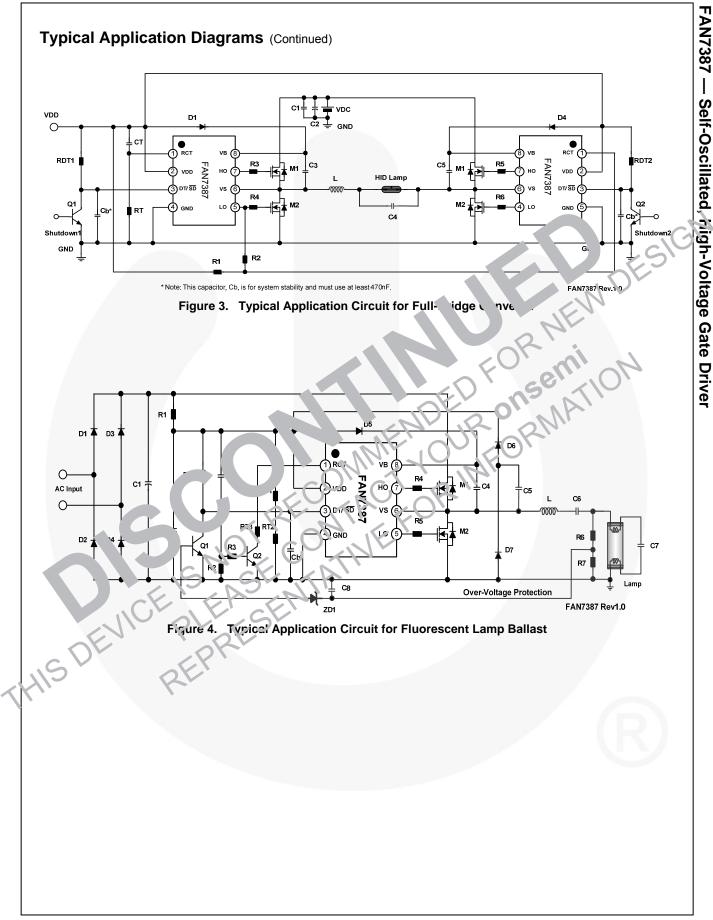
## Ord, ....g Information

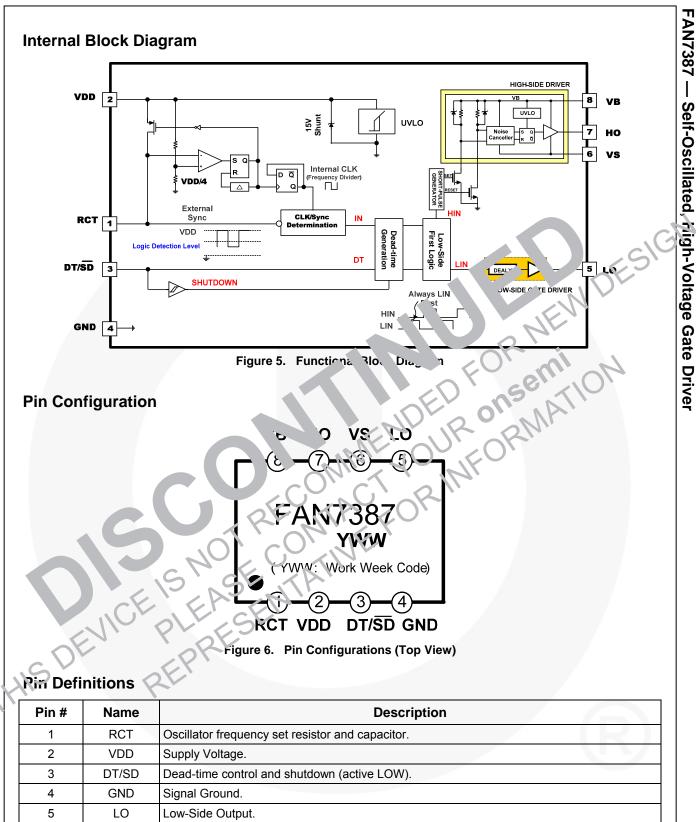
Part Number	Package	Operating Temperature	Packing Method
EAN'7?87MX <sup>(1)</sup>	8· SOP	-40 to +125°C	Tape & Reel

Note:

1. These device passed wave soldering test by JESD22A-111.







Name	Description
RCT	Oscillator frequency set resistor and capacitor.
VDD	Supply Voltage.
DT/SD	Dead-time control and shutdown (active LOW).
GND	Signal Ground.
LO	Low-Side Output.
VS	High-Side floating supply return.
HO	High-Side output.
VB	High-Side floating supply.
	RCT VDD DT/SD GND LO VS HO

FAN7387 — Self-Oscillated, high-Voltage Gate Driver

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. T<sub>A</sub>=25°C unless otherwise specified.

Symbol	Parameter	I	Min.	Тур.	Max.	Unit
V <sub>B</sub>	High-Side Floating Supply Voltage		-0.3		625.0	V
Vs	High-Side Offset Voltage		-0.3		600.0	V
V <sub>RCT</sub>	RCT Pins Input Voltage				V <sub>CL</sub>	V
I <sub>CL</sub>	Clamping current level <sup>(2)</sup>				25	mA
dV <sub>S</sub> /dt	Allowable Offset Voltage Slew Rate			50		V/ns
T <sub>A</sub>	Operating Temperature Range		-40		+ 5	°C
T <sub>STG</sub>	Storage Temperature Range		-65			°C
PD	Power Dissipation			J.625		W
$\Theta_{JA}$	Thermal Resistance (Junction-to-Air)				-11	°C/W

Note:

nin, Zen. 2. Do not supply a low-impedance voltage source to the internal .ode b -tw/een the GND and the VDD pin of this device. D Fonsemi IR ONATI

### Recommended Operating Patin, S

The Recommended Operating C ditions abil defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding the non-designing to absolute maximum ratings.

Symbol	Symbol Parameter		Max.	Unit.	
V <sub>B</sub>	່ງ-ວາວ ioating Supply Voltaຽe	V <sub>S</sub> +11	V <sub>S</sub> +14	V	
V <sub>s</sub>	Hir Side Cff. et Voltage	6-V <sub>DD</sub>	600	V	
V <sub>L</sub>	Low-Side Supply Voltage	11	14	V	
V <sub>HO</sub>	High-Side (HC) Output Voltage	GND	V <sub>DD</sub>	V	
	Low-Side ('-O) Output Voltage	GND	V <sub>DD</sub>	V	
VIE	Logic '1' input voltage of RCT	(3/4 V <sub>DD</sub> )+1		V	
V <sub>IL</sub>	Logic "0" http://voltage of RCT		(3/5 V <sub>DD</sub> )-1	V	
R <sub>T</sub>	Timing Resistor Value of RCT	2		kΩ	
Ст	Timing Capacitor Value of RCT	100		pF	
T <sub>A</sub>	Ambient Temperature	-40	+125	°C	

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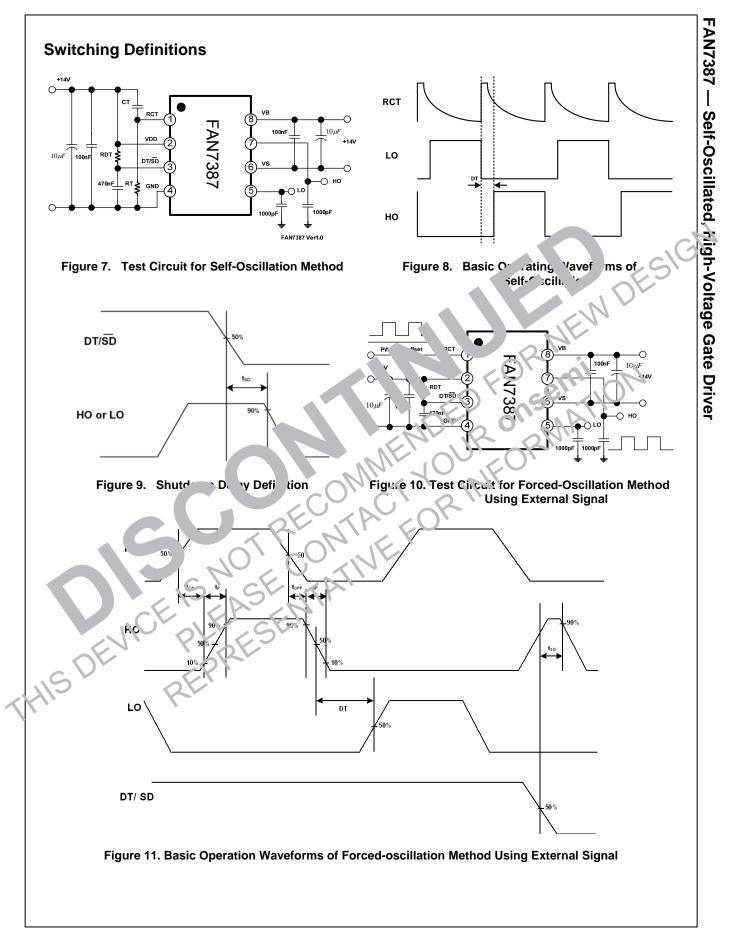
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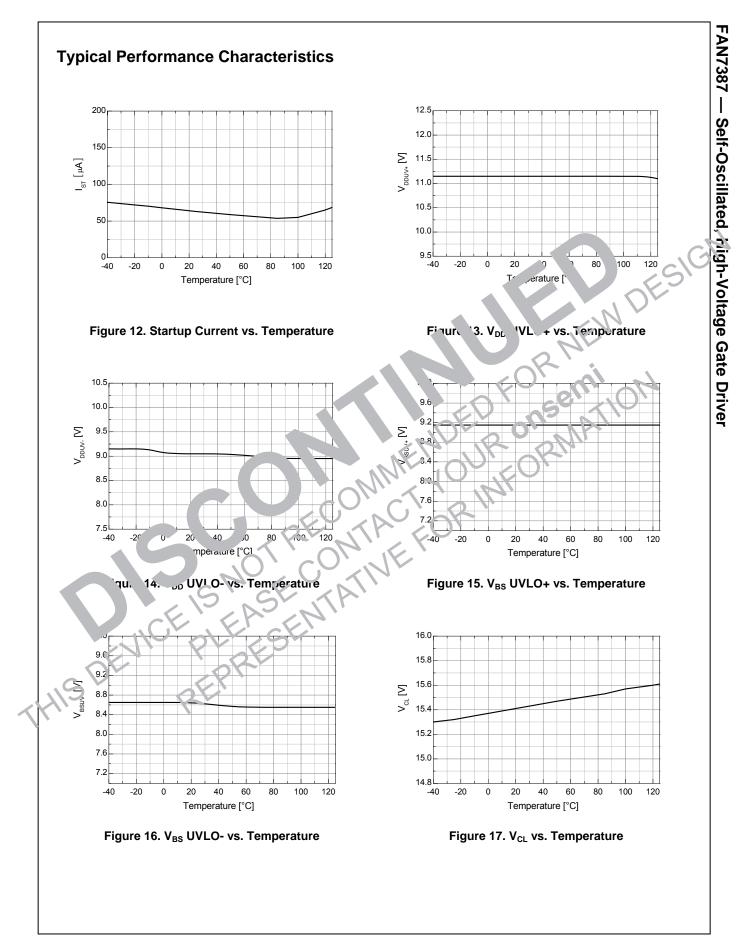
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Low-Sid	e Supply Characteristics (V <sub>DD</sub> )					
VDD <sub>UV+</sub>	V <sub>DD</sub> Supply Under-Voltage Positive-Going Threshold	V <sub>DD</sub> Increasing	9.50	11.00	12.50	V
VDD <sub>UV-</sub>	V <sub>DD</sub> Supply Under-Voltage Negative-Going Threshold	V <sub>DD</sub> Decreasing	7.5	9.0	10.5	V
VDD <sub>UVH</sub>	V <sub>DD</sub> Supply Under-Voltage Lockout Hysteresis			2		V
$V_{CL}$	Supply Camping Voltage	I <sub>DD</sub> =10 mA	14.8	15.4		V
I <sub>QDD</sub>	Low-Side Quiescent Supply Current	R <sub>DT</sub> =100 kΩ		<u></u>	500	μA
I <sub>ST</sub>	Startup Supply Current	V <sub>DD</sub> =9 V		50	130	цА
I <sub>LK</sub>	Offset Supply Leakage Current	V <sub>B</sub> =V <sub>S</sub> =600 V			10	μA
I <sub>PDD</sub>	Low-Side Dynamic Operating Supply Current			0.8		mA
High-Sic	le Supply Characteristics (V <sub>B</sub> -V <sub>S</sub> )			C/	7	
VBS <sub>UV+</sub>	V <sub>BS</sub> Supply Under-Voltage Negative-Going Threshold	VB-1 Inc. sir	7.7	9.2	10.7	V
VBS <sub>UV-</sub>	V <sub>BS</sub> Supply Under-Voltage Negative-Going Thresh	V <sub>B</sub> - creasing	7.1	8.1	10.1	V
VBS <sub>UVH</sub>	V <sub>BS</sub> Supply Under-Voltage Lockout Hysterer		~0	0.6		V
I <sub>QBS</sub>	High-Side Quiescent Supply Current			50	130	μA
I <sub>PBS</sub>	High-Side Dynamic Operating Su	NV R	10	400	800	μA
Oscillate	or Characteristics		)^_			
f <sub>osc1</sub>	Oscillation Freo	R <sub>T</sub> = 50 kΩ, C <sub>T</sub> =330 pF	18	20	22	kHz
f <sub>osc2</sub>	Oscillation Fre lency 2	R-=1 kΩ, C <sub>T</sub> =1 nF	210	250	290	kHz
D	Duty vel	Running Mode	47.5	49.0		%
V <sub>RCT</sub>	U, er Thres⁺.d Voltage of RCT	Running Mode		V <sub>DD</sub>		V
RCT-	w. Threshold Voltage of RCT	Running Mode		V <sub>DD</sub> /4		V
V <sub>h</sub>	ogic "4" Inout Voltage of RCT	Running Mode		3/4 V <sub>DD</sub>		V
V <sub>IL</sub>	Logic "0" Input Voltage ຈາ ໞຕາ	Running Mode			3/5 V <sub>DD</sub>	V
<u> </u>	Dead-Time	R <sub>DT</sub> =100 kΩ	500	600	700	ns
t <sub>DMIN</sub>	Minimum Dead-Time	V <sub>DT/SD</sub> =V <sub>DD</sub>	300	400	500	ns
Output (	Characteristics					$\sim$
I <sub>O+</sub>	Output High, Short-Circuit Pulse Current <sup>(3)</sup>	PW≤10 µs		350		mA
I <sub>O-</sub>	Output Low, Short-Circuit Pulse Current <sup>(3)</sup>	PW≤10 µs		650		mA
Vs	Allowable Negative $V_S$ Pin voltage for Input Signal ( $V_{RCT}$ ) Propagation to HO			-9.8	-7.0	v

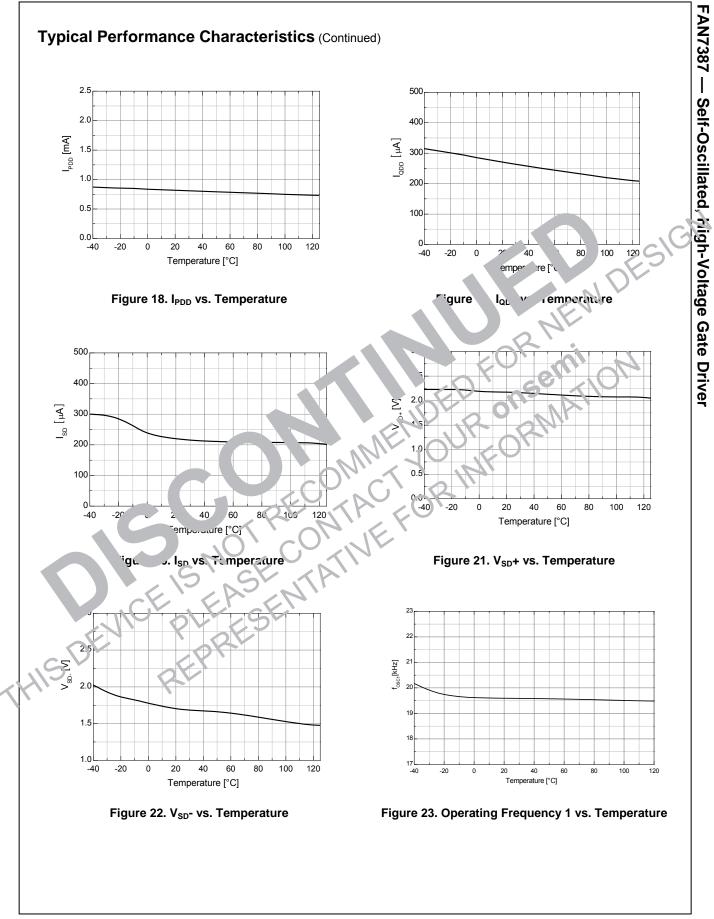
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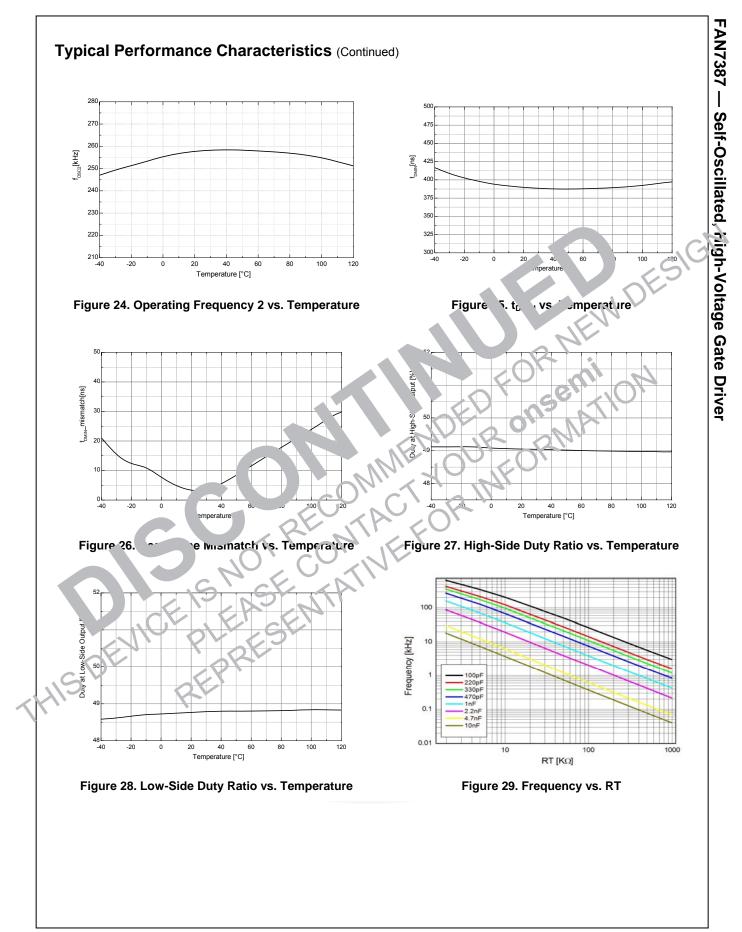
#### V<sub>BIAS</sub> (V<sub>DD</sub>, V<sub>B</sub> -V<sub>S</sub>)=14.0 V, C<sub>L</sub>=1 nF, R<sub>T</sub>=50 kΩ and C<sub>T</sub>=330 pF and T<sub>A</sub>=25°C, unless otherwise specified. Symbol Min. Unit Parameter Conditions Тур. Max. **Output Characteristics** $V_{DD}=V_{BS}=14 V, V_{DT/SD}=V_{DD}, V_{RCT}=4 V \sim V_{DD}, f_{OSC}=20 \text{ kHz}$ t<sub>on</sub> **Turn-On Propagation Time** 550 ns $V_{DD}=V_{BS}=14 V, V_{DT/SD}=V_{DD},$ **Turn-Off Propagation Time** 160 ns toFF V<sub>RCT</sub>=4 V~V<sub>DD</sub>, f<sub>OSC</sub>=20 kHz C<sub>L</sub>=1000 pF 120 Turn-On Rising Time 50 ns t<sub>R</sub> 70 t⊧ Turn-Off Falling Time C<sub>1</sub>=1000 pF ns **Protection Characteristics** V /SD+ Shutdown "1" Input Voltage /SD-V Shutdown "0" Input Voltage V<sub>DT/SD</sub>=0 After Running L de μA Shutdown Current 250 $I_{SD}$ ASENTATIVE FOR INFORMATI Shutdown Propagation Delay 180 t<sub>SD</sub> ns Note: These parameters, although guaranteed, is not 1 , tested 3. IS DEVICE IS NOT F

Electrical Characteristics (Continued)









### **Functional Description**

#### 1. Under-Voltage Lockout (UVLO) Function

FAN7387 has a UVLO circuit for a low-side and highside block. When  $V_{DD}$  reaches to the VDD<sub>UV</sub>+, the UVLO circuit is released and the FAN7387 operates normally. At UVLO condition, the FAN7387 has a low supply current of less than 130  $\mu A.$  Once UVLO is released, FAN7387 operates normally until  $V_{DD}$  goes below VDD<sub>UV</sub>-, the UVLO hysteresis.

FAN7387 also has a high-side gate driver. The supply for the high-side driver is applied between V<sub>B</sub> and V<sub>S</sub>. To prevent malfunction at low supply voltage between V<sub>B</sub> and V<sub>S</sub>, FAN7387 provides an additional UVLO circuit. If V<sub>B</sub>-V<sub>S</sub> is under VBS<sub>UV</sub>+, the driver holds LOW state to turn off the high-side switch. Once the voltage of V<sub>B</sub>-V<sub>S</sub> is higher than VBS<sub>UVH</sub>, after V<sub>B</sub>-V<sub>S</sub> exceeds VBS<sub>UV</sub>-, the operation of driver resumes.

#### 2. Oscillator

The running frequency is determined by an external timing resistor ( $R_T$ ) and timing capacitor ( $C_T$ ). The charge time of capacitor  $C_T$  from 1/4  $V_{DD}$  to  $V_{DD}$  determines the running frequency of LO and HO gate driver output. Figure 30 shows connection configuration

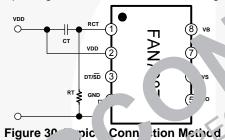


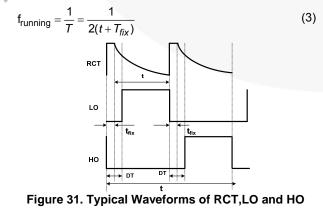
Figure 31 show the fall waveforms of RCT, LC, and HO. From a circuit a lysis, the discharging time of RCT give by a uon 1:

$$V_{\mathsf{h}} = V_{D_{\mathsf{h}}} < In(\frac{-t}{R_t \times C_t})$$

Equation 1 enables calculation of distributing time, t, from  $V_{DD}$  to  $1/4~V_{DD}$  by substituting  $V_{POT(f)}$  with  $1/4~V_{DD}$ 

$$= 1.38 \times R_t \times C_t \tag{2}$$

The running frequency of IC is determined by 1/T and is approximately given as:

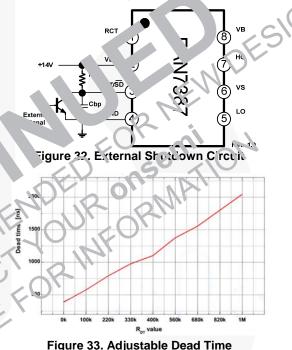


where, t is the discharging time of the RCT voltage and  $t_{\mbox{\scriptsize fix}}$  is constant value about 450 ns of IC.

#### 3. Programming Dead-Time Control / Shutdown

A multi-function pin controls dead-time using an external resistor ( $R_{\text{DT}}$ ) and protects abnormal condition using an external switch. This pin should be connected to an external capacitor to maintain stable operation.

If the voltage of DT/SD is decreased under 1 V by an external switch, such as the TR or MOSFET, the FAN7387 enters shutdown mode. In this mode, the FAN7387 doesn't have any output signal.



#### 4. Gate Driver Operation

The FAN7387 has a two operating modes. One is the self-oscillation mode by using external timing resistor ( $R_T$ ) and external timing capacitor ( $C_T$ ) and the other is the forced oscillation mode by external PWM signal comes from U-com and the other devices.

Figure 33 shows operation of the IC using an external PWM circuit with additional resistors (R1 and R2) for internal limitation of the IC. The input signal range from an external circuit must be within 3/5  $V_{DD}$  and 3/4  $V_{DD}$ . The external signal produces the HO and LO output and HO signal is in-phase with the external input signal.

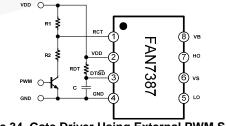
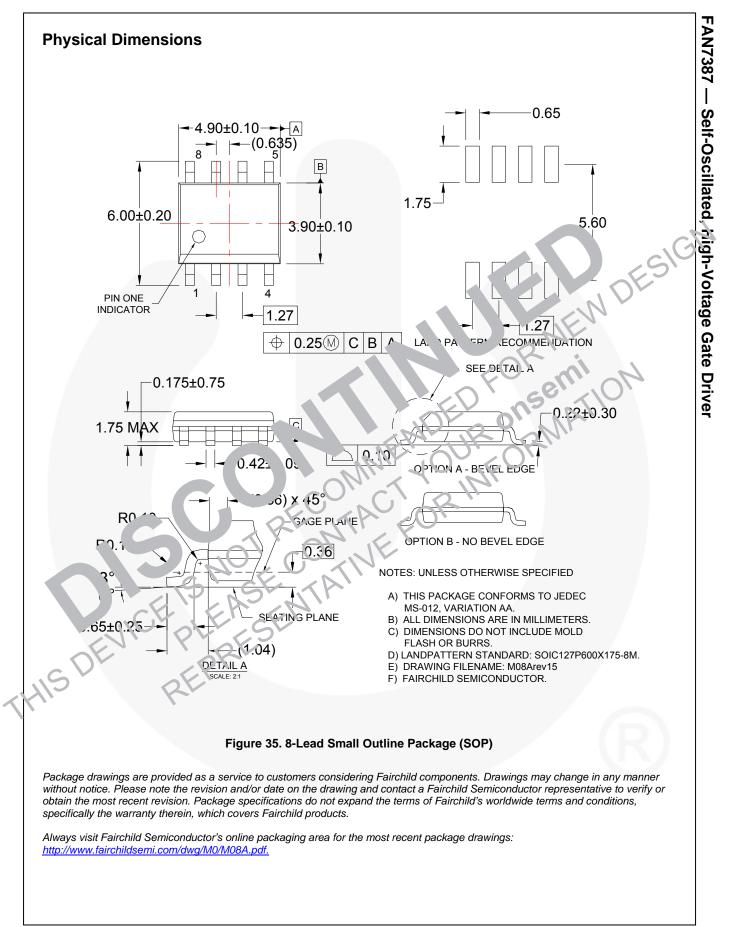


Figure 34. Gate Driver Using External PWM Signal





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